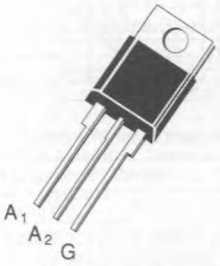
SGS-THOMSON MICROELECTRONICS

TXDV 208 → 808

ALTERNISTORS

- $(di/dt)_c$ > 28 A/ms (400 Hz)
- INSULATING VOLTAGE : 2500 V_{RMS} ($t \leq 1$ mn - F = 50 Hz)
- UL RECOGNIZED (E81734)



TO 220 AB
(Plastic)

APPLICATIONS

- POWER CONTROL ON INDUCTIVE LOAD (motor, transformer...)
- HIGH FREQUENCY OR HIGH $(di/dt)_c$ LEVEL CIRCUITS

DESCRIPTION

New range of solid state AC - switches with very high commutating capability.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state Current (360° conduction angle)	T_C = 75 °C	8	A
I_{TSM}	Non Repetitive Surge Peak on-state Current	t = 10 ms	80	A
		t = 8.3 ms	85	
		t = 2.5 ms	115	
I^2t	I^2t Value for Fusing	t = 10 ms	32	A^2s
di/dt	Critical Rate of Rise of on-state Current (1)		100	A/µs
T_{stg} T_j	Storage and Operating Junction Temperature Range		– 40 to 150 – 40 to 110	°C °C

Symbol	Parameter	TXDV				Unit
		208	408	608	808	
V_{DRM}	Repetitive Peak off-state Voltage (2)	200	400	600	800	V

(1) I_G = 1 A di_G/dt = 1 A/µs
(2) T_j = 110 °C.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th\ (j-a)}$	Junction to Ambient	60	°C/W
$R_{th\ (j-c)}$ DC	Junction to Case for DC	4	°C/W
$R_{th\ (j-c)}$ AC	Junction to Case for 360° Conduction Angle (F = 50 Hz)	3	°C/W

GATE CHARACTERISTICS (maximum values)

P_{GM} = 40 W (t_p = 10 µs) I_{GM} = 4 A (t_p = 10 µs)

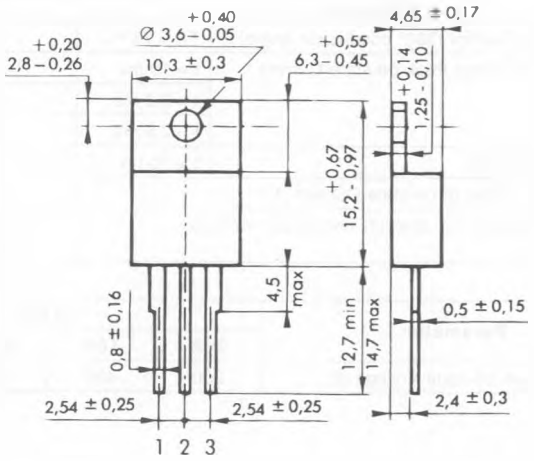
$P_{G(AV)}$ = 1 W V_{GM} = 16 V (t_p = 10 µs)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Quadrants	Min.	Typ.	Max.	Unit
I_{GT}	T_j = 25 °C V_D = 12 V R_L = 33 Ω Pulse Duration > 20 µs			I-II-III			100	mA
V_{GT}	T_j = 25 °C V_D = 12 V R_L = 33 Ω Pulse Duration > 20 µs			I-II-III			1.5	V
V_{GD}	T_j = 110 °C V_D = V_{DRM} R_L = 3.3 kΩ			I-II-III	0.2			V
I_H*	T_j = 25 °C I_T = 500 mA Gate Open						100	mA
I_L	T_j = 25 °C V_D = 12 V I_G = 200 mA Pulse Duration > 20 µs			I-III		100		mA
				II		200		
V_{TM}*	T_j = 25 °C I_{TM} = 11 A t_p = 10 ms						1.8	V
I_{DRM}*	T_j = 110 °C V_{DRM} Specified						2	mA
dv/dt*	T_j = 110 °C Gate Open Linear Slope up to V_D = 67 % V_{DRM}				500			V/µs
$(di/dt)_c$*	T_C = 75 °C V_D = V_{DRM} I_T = 11 A		$(dv/dt)_c$ = 200 V/µs		7			A/ms
			$(dv/dt)_c$ = 10 V/µs		28			
t_{gt}	T_j = 25 °C V_D = V_{DRM} I_T = 11 A I_G = 0.5 A di_G/dt = 3.5 A/µs			I-II-III		2.5		µs

* For either polarity of electrode A_2 voltage with reference to electrode A_1.

PACKAGE MECHANICAL DATA : TO 220 AB Plastic



Triac : 1 2 3 = A_1 A_2 G

Cooling method : by conduction (method C)
Marking : type number
Weight : 2 g

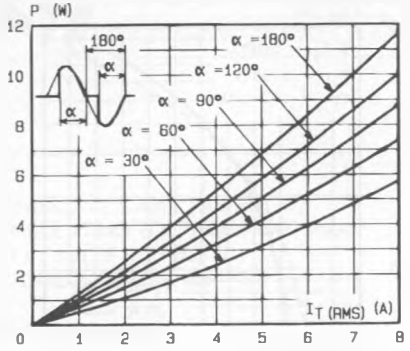


Fig.1 - Maximum mean power dissipation versus RMS on-state current.

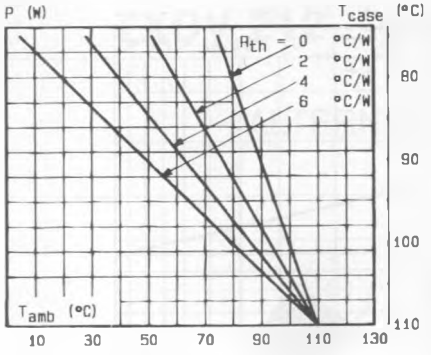


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

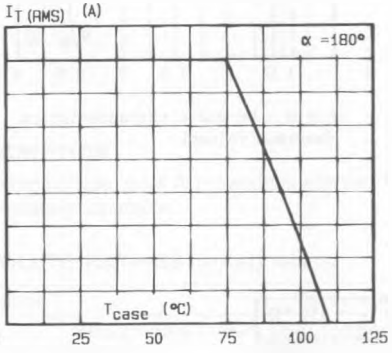


Fig.3 - RMS on-state current versus case temperature.

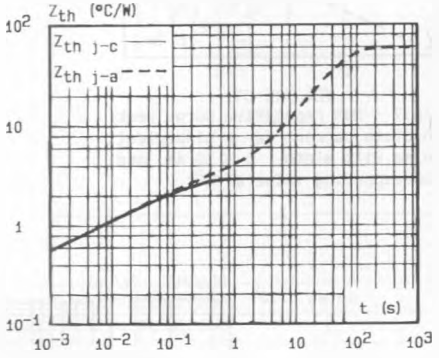


Fig.4 - Thermal transient impedance junction to case and junction to ambient versus pulse duration.

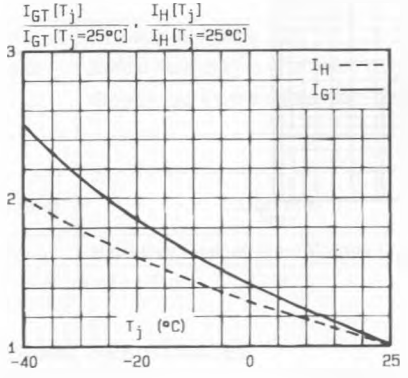


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

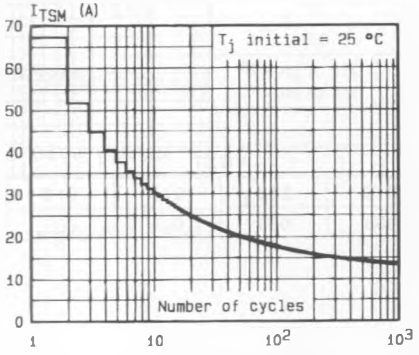


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

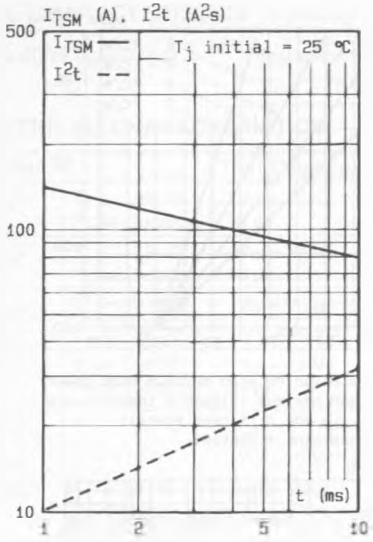


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : t ≤ 10 ms, and corresponding value of I^2t.

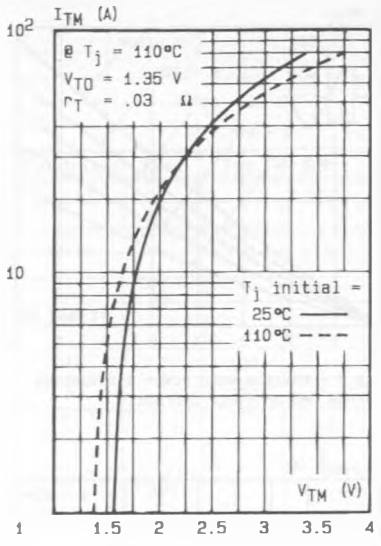


Fig.8 - On-state characteristics (maximum values).

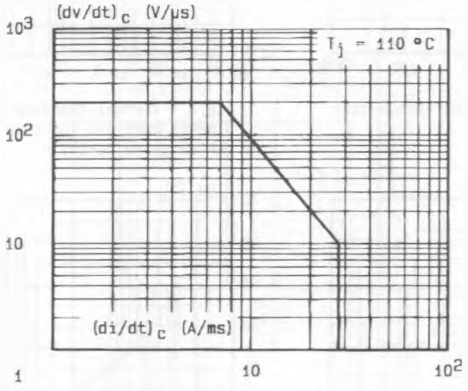


Fig.9 - Safe operating area.